

Amendments to the Specification

Paragraph at page 1, lines 5 and 6:

This application is a continuation of Serial No. 09/792,989, filed February 26, 2001 and now to be issued as U.S. Patent 6,727,191.

Paragraph at page 5, lines 2-12:

According to one aspect of the invention, a tower or boat used to support wafers in a high-temperature anneal of stock silicon wafers has at least support surfaces formed of silicon, preferably polysilicon, and more preferably virgin polysilicon. Boyle et al. have disclosed the fabrication of such a tower in U.S. Patent Application, Serial No. 09/608,291, filed June 30, 2000, now issued as U.S. Patent 6,455,395, and incorporated herein by reference in its entirety. Virgin polysilicon is polycrystalline silicon formed by the chemical vapor deposition (CVD) of silane and/or chlorosilane. Virgin polysilicon is conventionally used as the source material for the Czochralski growth of monocrystalline silicon ingots. Although trichlorosilane (CHCl_3) is the most prevalently used CVD precursor for semiconductor applications, virgin polysilicon formed from monosilane (SiH_4) is preferred for towers because of the absence of trace amounts of chlorine. Virgin polysilicon of extraordinarily high purity is commercially available.